

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

PETRUS H.C. MAGNEE ET AL

NL 000549

Serial No.

Filed: CONCURRENTLY

PROTECTION DIODE FOR IMPROVED RUGGEDNESS OF A RADIO FREQUENCY
POWER TRANSISTOR AND SELF-DEFINING METHOD TO MANUFACTURE SUCH
PROTECTION DIODE

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination,
please amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

3. (Amended) The arrangement according to claim 1, wherein said second diffusion region (45) is an anode of a protection diode (9) and said second buried layer (12) is a cathode of said protection diode (9).
4. (Amended) The arrangement according to claim 1, wherein said first buried layer (12) is connected to said second buried layer (12), and said first and second buried layers (12) are manufactured in the same step.
5. (Amended) The arrangement according to claim 1, further comprising a channel stopper region (42) in said second portion of said substrate layer (13); the channel stopper